# 2SC5440

# Silicon NPN triple diffusion mesa type

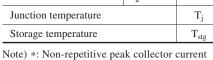
### For horizontal deflection output

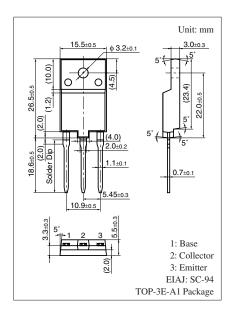
#### ■ Features

- High breakdown voltage, and high reliability through the use of a glass passivation layer
- High-speed switching
- Wide safe operation area (ASO)

## ■ Absolute Maximum Ratings $T_C = 25$ °C

Parameter	Symbol	Rating	Unit	
Collector-base voltage (Emitter open)	V <sub>CBO</sub>	1 500	V	
Collector-emitter voltage (E-B short)	V <sub>CES</sub>	1 500	V	
Collector-emitter voltage (Base open)	V <sub>CEO</sub>	600	V	
Emitter-base voltage (Collector open)	$V_{EBO}$	7	V	
Base current	$I_{B}$	7.5	A	
Collector current	$I_C$	15	A	
Peak collector current *	$I_{CP}$	25	A	
Collector power dissipation	P <sub>C</sub>	60	W	
$T_a = 25$ °C		3.0		
Junction temperature	$T_j$	150	°C	
Storage temperature	$T_{stg}$	-55 to +150	°C	



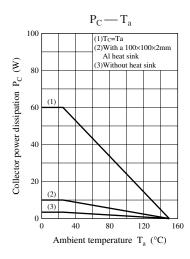


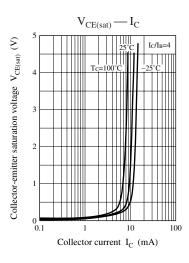
## ■ Electrical Characteristics $T_C = 25$ ° $C \pm 3$ °C

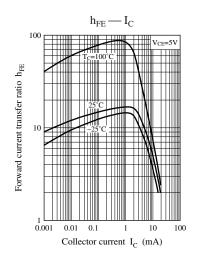
Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Collector-base cutoff current (Emitter open)	$I_{CBO}$	$V_{CB} = 1000 \text{ V}, I_{E} = 0$			50	μΑ
		$V_{CB} = 1500 \text{ V}, I_{E} = 0$			1	mA
Emitter-base cutoff current (Collector open)	$I_{EBO}$	$V_{EB} = 7 \text{ V}, I_{C} = 0$			50	μΑ
Forward current transfer ratio	$h_{FE}$	$V_{CE} = 5 \text{ V}, I_{C} = 7.5 \text{ A}$	5		9	_
Collector-emitter saturation voltage	V <sub>CE(sat)</sub>	$I_C = 7.5 \text{ A}, I_B = 1.88 \text{ A}$			3	V
Base-emitter saturation voltage	V <sub>BE(sat)</sub>	$I_C = 7.5 \text{ A}, I_B = 1.88 \text{ A}$			1.5	V
Transition frequency	$f_T$	$V_{CE} = 10 \text{ V}, I_{C} = 0.1 \text{ A}, f = 0.5 \text{ MHz}$		3		MHz
Storage time	t <sub>stg</sub>	$I_C = 7.5$ A, Resistance loaded			2.7	μs
Fall time	$t_{\rm f}$	$I_{B1} = 1.88 \text{ A}, I_{B2} = -3.76 \text{ A}$			0.2	μs

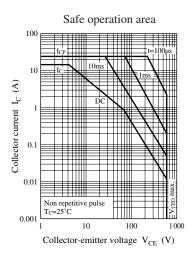
Note) Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

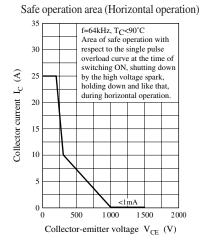
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